

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L10	2	"20020109958"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:40
L11	12	"6370011"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:43
L12	9	"6462932"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:44
L13	7	"6496354"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:44
L14	12	"6549395"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:45
L15	52	"6034864"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:48
L16	39	"361"/\$.ccls. and (semiconductor adj device with interposed with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:57
L17	1929	(semiconductor adj device with interposed with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:50

## EAST Search History

L18	128	17 and(first adj surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:50
L19	109	18 and(second adj surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:50
L20	5	19 and(conductive adj via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:51
L21	9	17 and(conductive adj via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:52
L22	329	361/306.2 and(capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:53
L23	149	22 and(semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:19
L24	143	23 and(via through)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:54
L25	9	24 and(main adj body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:53

## EAST Search History

L26	1421	"257"/\$.ccls. and(semiconductor adj device with interposed with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:21
L27	7	26 and(conductive adj via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:59
L28	417	26 and(capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 14:59
L29	3267192	28(via\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:00
L30	197	28 and(via\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:06
L31	23026	semiconductor adj device.ti. and(capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:07
L32	63	31 and(conductive adj via\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:07
L33	1	"20020109958".PN.	US-PGPUB	OR	OFF	2006/08/16 15:15
L34	1	"6606237".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:16
L35	1	"6577490" PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:16
L36	1	"6549395".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17

## EAST Search History

L37	1	"6496354".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17
L38	1	"6462932".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17
L39	1	"6370011".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17
L40	1	"6351369".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17
L41	1	"6282079".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17
L42	1	"6259593".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17
L43	1	"6034864".PN.	USPAT; USOCR	OR	OFF	2006/08/16 15:17
L44	8	otsuka adj jun in. and(semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:20
L45	575	"438"/\$.ccls. and(semiconductor adj device with interposed with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:21
L46	575	45 and(semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:21
L47	526	46 and(conductive adj via\$1 or through)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:22
L48	526	47 and(substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:22

## EAST Search History

L49	20	48 and(main adj body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:23
L50	18	sato:adj manabu.in: and(semiconductor adj device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:39
L51	10499	capacitor.ti. and(semiconductor adj device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:40
L52	958	51 and(terminal\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:40
L53	30	52 and(conductive adj via\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:45
L54	8497	semiconductor adj device and IC adj chip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:45
L55	180	54 and(conductive adj via\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:53
L56	34	conductive adj via\$1 adj penetrat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 15:53